

NDC7002N

Dual N-Channel Enhancement Mode Field Effect Transistor

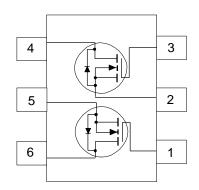
General Description

These dual N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. These devices is particularly suited for low voltage applications requiring a low current high side switch.

Features

- 0.51A, 50V, $R_{DS(ON)} = 2\Omega$ @ $V_{GS}=10V$
- High density cell design for low R_{DS(ON)}.
- Proprietary SuperSOTTM-6 package design using copper lead frame for superior thermal and electrical capabilities.
- High saturation current.

D1 D2 G2 G2 G1 SOT-6 (SuperSOT[™]-6)



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		NDC7002N	Units
V _{DSS}	Drain-Source Voltage		50	V
V _{GSS}	Gate-Source Voltage - Continuous		20	V
I _D	Drain Current - Continuous	(Note 1a)	0.51	Α
	- Pulsed		1.5	
P _D	Maximum Power Dissipation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 150	°C
THERMA	L CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHA	RACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		50			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$				1	μΑ
			T _J = 125°C			500	
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHAP	RACTERISTICS (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		1	1.9	2.5	V
			T _J = 125°C	0.8	1.5	2.2	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 0.51 \text{ A}$			1	2	Ω
			T _J = 125°C		1.7	3.5	
		$V_{GS} = 4.5 \text{ V}, I_D = 0.35 \text{ A}$	$V_{GS} = 4.5 \text{ V}, I_D = 0.35 \text{ A}$				
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 10 V	1.5			Α	
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 0.51 \text{ A}$		400		mS	
DYNAMIC	CHARACTERISTICS						
C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, \ V_{GS} = 0 \text{ V},$		20		pF	
C _{oss}	Output Capacitance	f = 1.0 MHz		13		pF	
C _{rss}	Reverse Transfer Capacitance			5		pF	
	NG CHARACTERISTICS (Note 2)					ı	
t _{D(on)}	Tum - On Delay Time	$V_{DD} = 25 \text{ V}, I_{D} = 0.25 \text{ A},$		6	20	nS	
t,	Turn - On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 25 \Omega$		6	20		
t _{D(off)}	Turn - Off Delay Time			11	20		
t _f	Turn - Off Fall Time			5	20		
Q _g	Total Gate Charge	V _{DS} = 25 V,		1		nC	
Q_{gs}	Gate-Source Charge	$I_D = 0.51 \text{ A}, V_{GS} = 10 \text{ V}$		0.19		nC	
Q _{gd}	Gate-Drain Charge			0.33		nC	

ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted)									
Symbol	Parameter Conditions Min Typ Max								
DRAIN-SOURCE DIODE CHARACTERISTICS									
Is	Maximum Continuous Source Current 0.51								
I _{SM}	Maximum Pulse Source Current (Note 2)			1.5	Α				
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 0.51 \text{ A (Note 2)}$		0.8	1.2	V			

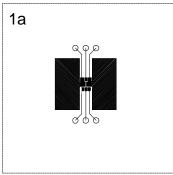
Notes:

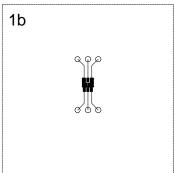
1. R_{gut} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{gut} is guaranteed by design while R_{gut} is determined by the user's board design.

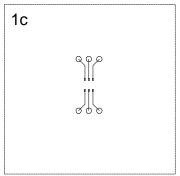
$$P_{D}(t) = \frac{T_{J} - T_{A}}{R_{\theta J} \, \hat{A}^{(t)}} = \frac{T_{J} - T_{A}}{R_{\theta J} \, \hat{c}^{\dagger} R_{\theta C} \hat{A}^{(t)}} = I_{D}^{2}(t) \times R_{DS(ON) \hat{\theta} T_{J}}$$

Typical R_{BJA} for single device operation using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- a. 130°C/W when mounted on a $0.125~\text{in}^2$ pad of 2oz cpper.
- b. 140°C/W when mounted on a 0.005 in 2 pad of 2oz cpper.
- c. 180°C/W when mounted on a 0.0015 in 2 pad of 2oz cpper.







Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

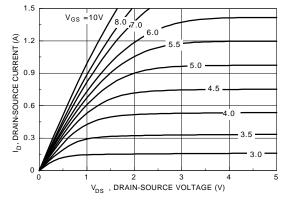


Figure 1. On-Region Characteristics.

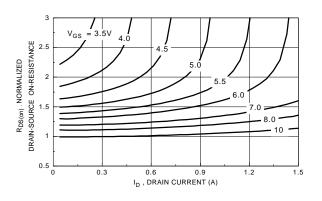


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

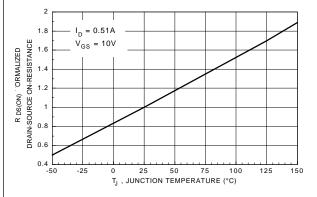


Figure 3. On-Resistance Variation with Temperature.

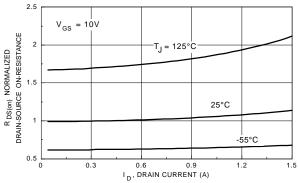


Figure 4. On-Resistance Variation with Drain Current and Temperature.

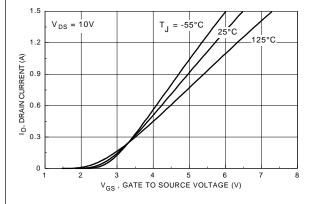


Figure 5. Transfer Characteristics.

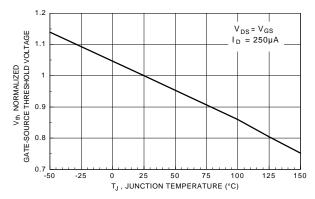


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

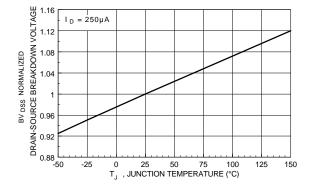


Figure 7. Breakdown Voltage Variation with Temperature.

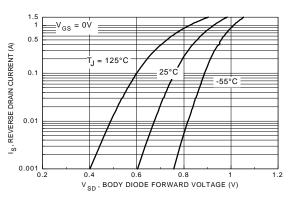


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

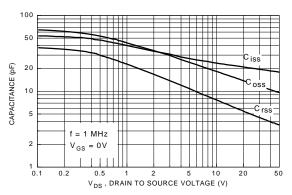


Figure 9. Capacitance Characteristics.

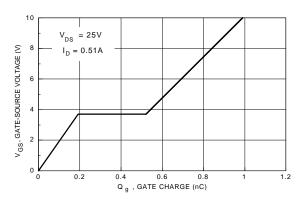


Figure 10. Gate Charge Characteristics.

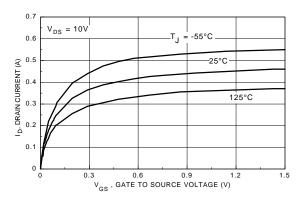


Figure 11. Transconductance Variation with Drain Current and Temperature.

Typical Thermal Characteristics

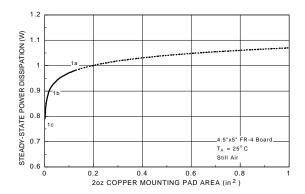


Figure 12. SOT-6 Dual Package Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.

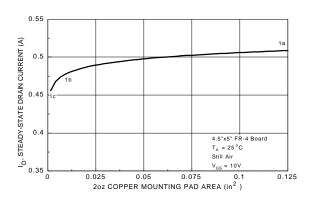


Figure 13. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

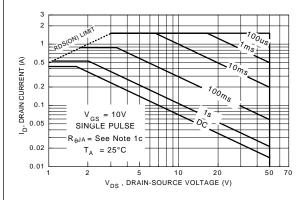


Figure 14. Maximum Safe Operating Area.

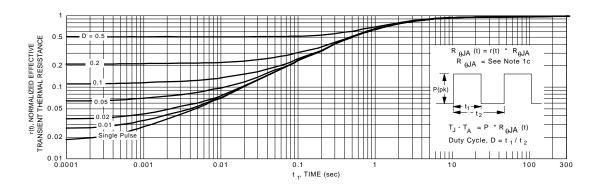
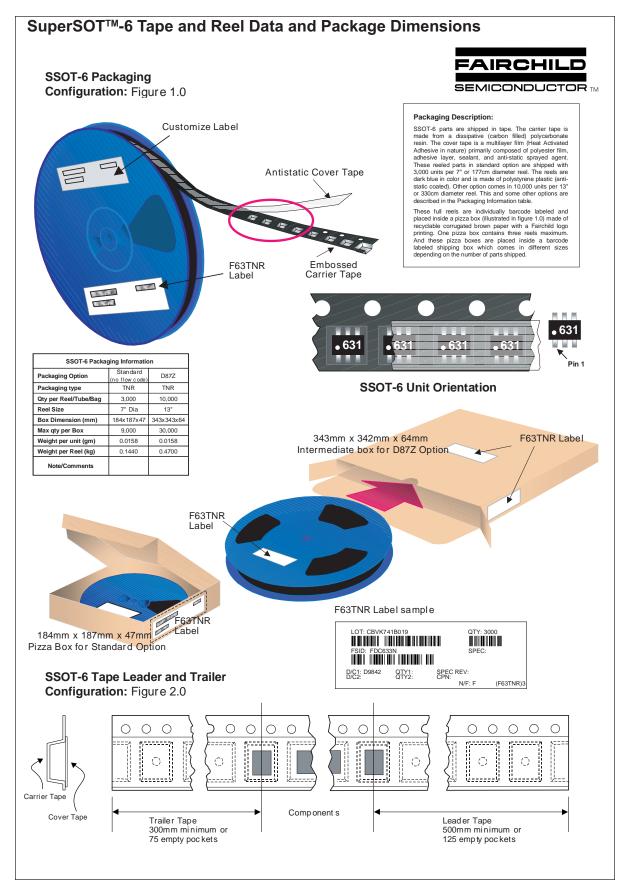
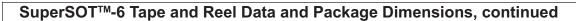


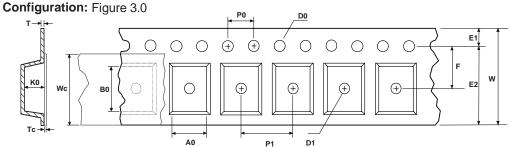
Figure 15. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.





SSOT-6 Embossed Carrier Tape



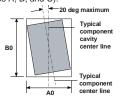


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

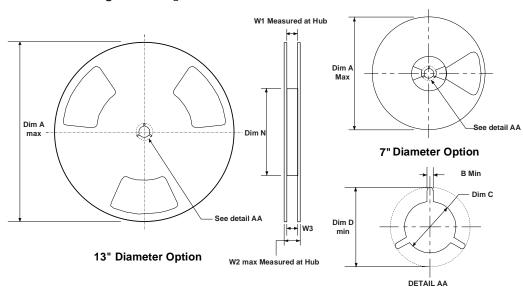


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

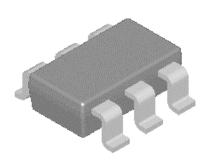
SSOT-6 Reel Configuration: Figure 4.0

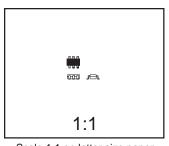


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

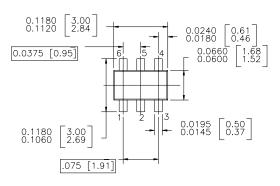
SuperSOT -6 (FS PKG Code 31, 33)

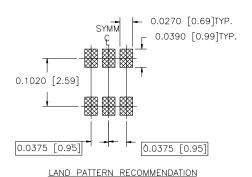




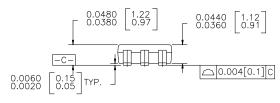
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

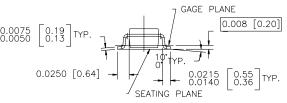
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$

SUPER SOT 6 LEADS

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